

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. (currently amended): A ~~pn~~ pn junction type Group III nitride semiconductor light-emitting device ~~having comprising~~ a light-emitting layer of multiple quantum well structure in which well layers and barrier layers including Group III nitride semiconductors are alternately stacked periodically between an n-type clad layer and a p-type clad layer which are formed on a crystal substrate and which include Group III nitride semiconductors,

wherein ~~one~~ a first end layer of the light-emitting layer is closest to and opposed to the n-type clad layer, and ~~the other~~ a second end layer of the light-emitting layer is closest to and opposed to the p-type clad layer, both the ~~one~~ and the ~~other~~ first and second end layers are barrier layers, and the ~~other~~ second end layer is thicker than the barrier layer of the ~~one~~ first end layer.

2. (currently amended): The pn junction type Group III nitride semiconductor light-emitting device according to claim 1, wherein each of the barrier layers has a thickness increased gradually from the ~~one~~ first end layer toward the ~~other~~ second end layer.

3. (currently amended): The pn junction type ~~GROUP~~ Group III nitride semiconductor light-emitting device according to claim 1, wherein the ~~other~~ second end layer has an impurity concentration low at its junction portion relative to the well layer, highest at its central portion and reduced gradually from the central portion toward the p- type clad layer.

4. (currently amended): The pn junction type-~~GROUP~~ Group III nitride semiconductor light-emitting device according to claim 1, wherein the ~~other~~ second end layer has joined thereto a well layer which. is not intentionally doped with impurities.